

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	"6682944".pn.	USPAT	OR	OFF	2005/01/05 14:32
S1	1	"4463030".pn.	USPAT	OR	OFF	2005/01/03 18:38
S2	1	"4780796".pn.	USPAT	OR	OFF	2005/01/04 08:53
S3	7417	semiconductor adj device.ti. and(insulat\$3 with silicon adj oxide)	US-PGPUB; USPAT	AND	OFF	2005/01/04 09:25
S4	3495	S3 and dielectric	US-PGPUB; USPAT	AND	OFF	2005/01/04 08:54
S5	93	S4 and top adj electrode	US-PGPUB; USPAT	AND	OFF	2005/01/04 08:55
S6	60	S5 and bottom adj electrode	US-PGPUB; USPAT	AND	OFF	2005/01/04 08:55
S7	218	semiconductor adj device.ti. and(insulat\$3 near silicon adj oxide)	US-PGPUB; USPAT	AND	OFF	2005/01/04 09:25
S8	4	S7 and S5	US-PGPUB; USPAT	AND	OFF	2005/01/04 09:27
S9	1	"6388281".pn.	US-PGPUB; USPAT	AND	OFF	2005/01/04 09:27
S10	7	("6388281").URPN:	USPAT	OR	OFF	2005/01/05 09:33
S11	209	semiconductor adj device.ti. and second adj capacitor	USPAT	OR	OFF	2005/01/05 10:31
S12	12	multiple adj capacitor.ti.	USPAT	OR	OFF	2005/01/05 10:31
S13	22	multiple adj capacitor and 361/328	USPAT	OR	OFF	2005/01/05 10:32
S14	612	361/328	USPAT	OR	OFF	2005/01/05 10:32
S15	104	S14 and second adj capacitor	USPAT	OR	OFF	2005/01/05 10:34
S16	3863	semiconductor adj device.ti. and capacitor	USPAT	OR	OFF	2005/01/05 10:34
S17	297	S16 and insulation adj layer	USPAT	OR	OFF	2005/01/05 14:32